

**/ Descriptions**

Silicon NPN transistor in a TO-126F Plastic Package.

**/ Features**

4W output in complementary pair with 2SA886.

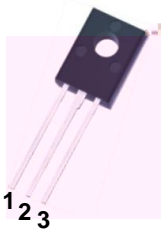
**/ Applications**

Medium power amplifier.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 Emitter      PIN 2 Collector      PIN 3 Base

**/  $h_{FE}$  Classifications & Marking**

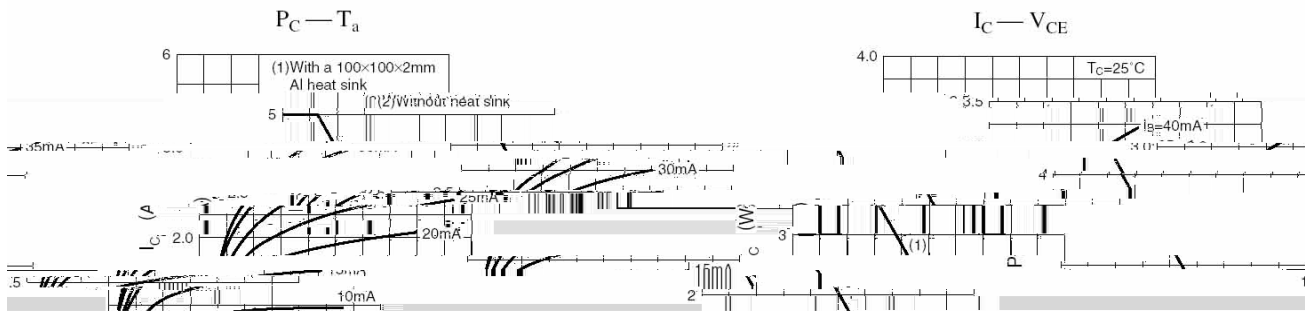
$h_{FE}$ Classifications Symbol	P	Q	R
$h_{FE}$ Range	50 100	80 160	120 220

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	50	V
Collector to Emitter Voltage	$V_{CEO}$	40	V
Emitter to Base Voltage	$V_{EBO}$	5.0	V
Collector Current - Continuous	$I_C$	1.5	A
Collector Current – Continuous(Pulse)	$I_{CP}$	3.0	A
Collector Power Dissipation	$P_C$	1.2	W
Collector Power Dissipation*	$*P_C(T_C=25^\circ C)$	5.0*	W
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

\*With a 100×100×20mm AL heat sink

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=1.0mA$ $I_E=0$	50			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=2.0mA$ $I_B=0$	40			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=20V$ $I_E=0$			1.0	A
Collector Cut-Off Current	$I_{CEO}$	$V_{CE}=10V$ $I_B=0$			100	A
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=5.0V$ $I_C=0$			10	A
	$I_{FE}$	$V_{CE}=5.0V$ $I_C=5mA$	1		0	A
$V_o$	$I_{CE(sat)}$	$V_{CB}=20V$ $I_E=0$	0	0	2	V
	$T_V$	$V_{CE}=5.0V$ $I_C=5mA$	0		5	A
		$V_{CB}=20V$ $I_E=0$ $f = 1000$ M H z				

/ Electrical Characteristic Curve



**2SC1847**

**/ Marking Instructions**



